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APR 10 2003

TECHNOLOGY CENTER 2800

**Fax**

**To:** Assistant Commissioner for Patents

**From:** David Bonham  
(703) 433-0510

**Fax:** 703-872-9319

**Total pages:** 11

**Phone:**

**Date:** 4/10/03

**Re:** In connection with prosecution in Serial. No.  
09/881,254, please find enclosed an Amendment  
and Response to the final Office Action mailed  
February 13, 2003.

**CC:**

Sincerely,

David Bonham

☐ **Urgent**    ☐ **For Review**    ☐ **Please Comment**    ☐ **Please Reply**    ☐ **Please Recycle**

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Please do Not enter. *[Signature]*  
Serial No. 09/881,254

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#10/B  
Andt  
NIE  
J. Macmillan  
4/16/03

Applicant: Fwu-Iuan Hshieh et al. ✓  
Serial No.: 09/881,254 ✓  
Filed: 06/14/2001 ✓  
Title: SYMMETRIC TRENCH MOSFET DEVICE AND METHOD OF MAKING SAME  
Art Unit: 2826  
Examiner: Mondt, Johannees P.  
Docket No.: GS 134  
VIA FACSIMILE 703-872-9319  
Box AF  
Assistant Commissioner for Patents  
Washington, D.C. 20231

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AMENDMENT AND RESPONSE

Sir:

Responsive to the outstanding Office Action dated February 13, 2003 in the above-identified patent application, please enter the following amendments and remarks:

IN THE CLAIMS:

Please amend claims 1 and 14 as follows:

1. (Amended) A trench MOSFET transistor device comprising:
- a drain region of a first conductivity type;
  - a body region of a second conductivity type provided over said drain region, said drain region and said body region forming a first junction;
  - a source region of said first conductivity type provided over said body region, said source region and said body region forming a second junction;
  - source metal disposed on an upper surface of said source region;

PLEASE ENTER (IN VIEW OF ACE)  
Thanks. *[Signature]* (5/31/03)

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